PERICOM

Fast CMOS 3.3V 20-Bit Transparent Latch

Product Features:

- Supports Mixed Signal Mode Operation
  - 5 Volt Input.
  - 5 Volt Output (when connected to a 5 Volt Bus).
  - Can serve as a 5 volt to 3 volt translator.
- Advanced Low Power CMOS process.
- Low Standby Current (Low power CMOS, not Bi-CMOS, so output drive transistors do not require bipolar standby current levels). Typical standby power 1 mW.
- Excellent output drive capability: Balanced drives (24 mA sink and source). Compatible with LVC™ class of products.
- Pin and functional compatible: Industry standard double-density pinouts.
- Low ground bounce outputs, hysteresis on all inputs.
- ESD Protection exceeds 2000 volts.
- Packaged in 56-pin plastic TSSOP and SSOP

Product Description:

Pericom Semiconductor's PI74FCT series of logic circuits are produced in the Company's advanced 0.8 micron CMOS technology, achieving industry leading speed grades.

The PI74FCT163841T is a 20-bit wide transparent latch designed to provide temporary storage of data and can be used as I/O port, memory address latch, and bus driver. The Output Enable and Latch Enable controls allows the device to be operated as two 10-bit latches or one 20-bit latch. Signal pins are arranged in a flow-through organization for ease of layout and hysteresis is designed into all inputs to improve noise margin.

The PI74FCT163841 can be driven from either 3.3 V or 5.0 V devices allowing this device to be used as a translator in a mixed 3.3/5.0 V system.

All products are available in 56-pin 240 mil wide plastic TSSOP and 300 mil wide plastic SSOP packages.

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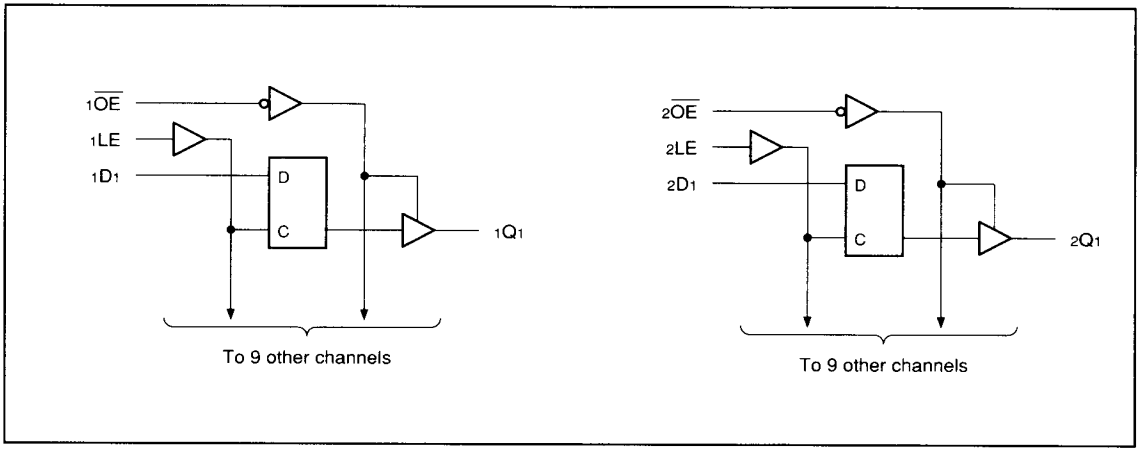
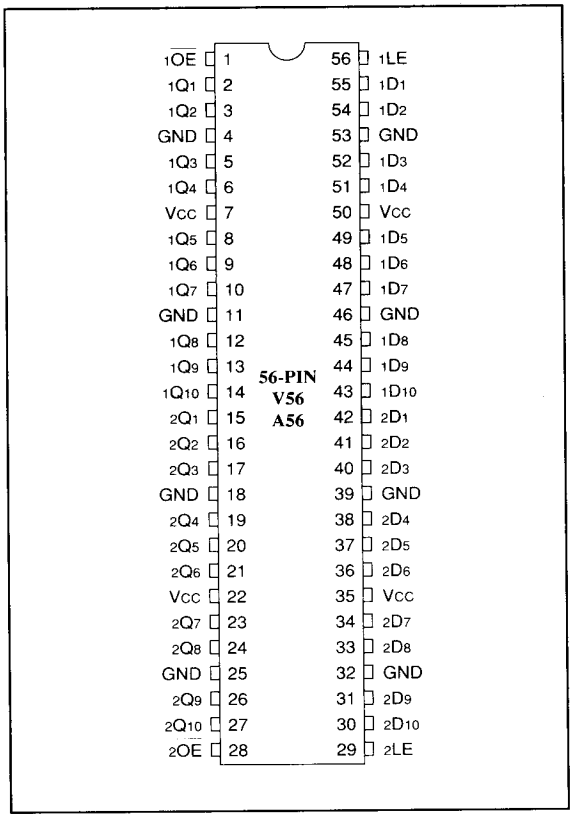
Logic Block Diagram



Product Configuration



Product Pin Description

Pin Name	Description
xDx	Data Inputs
xLE	Latch Enable Input (Active LOW)
xOE	Output Enable Input (Active LOW)
xQx	3-State Outputs

Truth Table[1]

Inputs			Outputs
xDx	xLE	xOE	xQx
H	H	L	H
L	H	L	L
X	L	L	Q[2]
X	X	H	Z

1. H = High Voltage Level
   L = Low Voltage Level
   X = Don't Care
   Z = High Impedance
2. Output level before xLE HIGH-to-LOW Transition.

Maximum Ratings

(Above which the useful life may be impaired. For user guidelines, not tested.)

Storage Temperature	–55°C to +125°C
Ambient Temperature with Power Applied	–40°C to +85°C
Supply Voltage to Ground Potential (Inputs & Vcc Only)	–0.5V to +7.0V
Supply Voltage to Ground Potential (Outputs & D/O Only)	–0.5V to Vcc
DC Input Voltage	–0.5V to +7.0V
DC Output Current	120 mA
Power Dissipation	1.0W

Note:
Stresses greater than those listed under MAXIMUM RATINGS may cause permanent damage to the device. This is a stress rating only and functional operation of the device at these or any other conditions above those indicated in the operational sections of this specification is not implied. Exposure to absolute maximum rating conditions for extended periods may affect reliability.

DC Electrical Characteristics (Over the Operating Range, T_A = –40°C to +85°C, V_{CC} = 3.3V ± 0.3V)

Parameters	Description	Test Conditions[1]		Min.	Typ[2]	Max.	Units
V_{IH}	Input HIGH Voltage (Input pins)	Guaranteed Logic HIGH Level		2.2		5.5	V
	Input HIGH Voltage (I/O pins)			2.0		5.5	V
V_{IL}	Input LOW Voltage (Input and I/O pins)	Guaranteed Logic LOW Level		–0.5		0.8	V
I_{IH}	Input HIGH Current (Input pins)	V_{CC} = Max.	V_{IN} = 5.5V			±5	µA
	Input HIGH Current (I/O pins)	V_{CC} = Max.	V_{IN} = V_{CC}			15	µA
I_{IL}	Input LOW Current (Input pins)	V_{CC} = Max.	V_{IN} = GND			±5	µA
	Input LOW Current (I/O pins)	V_{CC} = Max.	V_{IN} = GND			15	µA
I_{OZH}	High Impedance Output Current	V_{CC} = Max.	V_{OUT} = V_{CC}			10	µA
I_{OZL}	(3-State Output pins)	V_{CC} = Max.	V_{OUT} = GND			10	µA
V_{IK}	Clamp Diode Voltage	V_{CC} = Min., I_{IN} = –18 mA				–1.2	V
I_{ODH}	Output HIGH Current	V_{CC} = 3.3V, V_{IN} = V_{IH} or V_{IL}, V_O = 1.5V[3]		–36		–110	mA
I_{ODL}	Output LOW Current	V_{CC} = 3.3V, V_{IN} = V_{IH} or V_{IL}, V_O = 1.5V[3]		50		200	mA
V_{OH}	Output HIGH Voltage	V_{CC} = Min.	I_{OH} = –0.1mA	Vcc-0.2			V
		V_{IN} = V_{IH} or V_{IL}	I_{OH} = –8mA	2.4			V
			I_{OH} = –24mA	2.0			V
V_{OL}	Output LOW Voltage	V_{CC} = Min.	I_{OL} = 0.1mA			0.2	V
		V_{IN} = V_{IH} or V_{IL}	I_{OL} = 16mA			0.4	V
			I_{OL} = 24mA			0.5	V
I_{OS}	Short Circuit Current[4]	V_{CC} = Max.[3], V_{OUT} = GND		–60	–135	–240	mA
I_{OFF}		V_{CC} = 0V, V_{IN} or V_{OUT} = 4.5V				100	µA
V_H	Input Hysteresis				150		mV
I_{CCL}	Quiescent Power Supply Current	V_{CC} = Max., V_{IN} = GND or V_{CC}				1.5	mA
I_{CCH}							
I_{CCZ}							

Notes:
1. For conditions show as Max. or Min., use appropriate value specified under Electrical Characteristics for the applicable device type.
2. Typical values are at Vcc = 3.3, +25°C ambient and maximum loading.
3. Not more than one output should be shorted at one time. Duration of the test should not exceed one second.
4. This parameter is guaranteed but not tested.

Power Supply Characteristics

Parameters	Description	Test Conditions[1]		Min.	Typ[2]	Max.	Units
ΔI_{CC}	Quiescent Power Supply Current	V_{CC} = Max.	$V_{IN} = V_{CC} - 0.6$[3]		2.0	30	µA
	TTL Inputs HIGH		V_{IN} = 2.4 V[3]		70	500	µA
I_{CCD}	Dynamic Power Supply[4]	V_{CC} = Max., Outputs Open $x\overline{OE}$ = GND One Bit Toggling 50% Duty Cycle	$V_{IN} = V_{CC}$ V_{IN} = GND		50	75	µA/ MHz
I_C	Total Power Supply Current[6]	V_{CC} = Max., Outputs Open f_i = 10 MHz 50% Duty Cycle $x\overline{OE}$ = GND One Bit Toggling	$V_{IN} = V_{CC} - 0.6V$ V_{IN} = GND		0.6	2.3	mA
			V_{IN} = 2.4 V V_{IN} = GND		0.6	2.5	
		V_{CC} = Max., Outputs Open f_i = 2.5 MHz 50% Duty Cycle $x\overline{OE}$ = GND 16 Bits Toggling	$V_{IN} = V_{CC} - 0.6V$ V_{IN} = GND		2.1	4.7[5]	
			V_{IN} = 2.4 V V_{IN} = GND		2.6	8.5[5]	

Notes:

1. For conditions shown as Max. or Min., use appropriate value specified under Electrical Characteristics for the applicable device.
2. Typical values are at Vcc = 3.3 V, +25°C ambient.
3. Per TTL driven input (V_{IN} = 3.4 V); all other inputs at Vcc or GND.
4. This parameter is not directly testable, but is derived for use in Total Power Supply Calculations.
5. Values for these conditions are examples of the Icc formula. These limits are guaranteed but not tested.
6. $I_C = I_{QUIESCENT} + I_{INPUTS} + I_{DYNAMIC}$
   $I_C = I_{CC} + \Delta I_{CC} D_H N_T + I_{CCD} (f_{CP}/2 + f_i N_i)$
   I_{CC} = Quiescent Current (I_{CCL}, I_{CCH} and I_{CCZ})
   ΔI_{CC} = Power Supply Current for a TTL High Input
   D_H = Duty Cycle for TTL Inputs High
   N_T = Number of TTL Inputs at D_H
   I_{CCD} = Dynamic Current Caused by an Input Transition Pair (HLH or LHL)
   f_{CP} = Clock Frequency for Register Devices (Zero for Non-Register Devices)
   N_{CP} = Number of Clock Inputs at f_{CP}
   f_i = Input Frequency
   N_i = Number of Inputs at f_i
   All currents are in milliamps and all frequencies are in megahertz.

Switching Characteristics over Operating Range

Parameters	Description	Conditions[1]	FCT163841AT Com. Min	FCT163841AT Com. Max	Unit
t_{PLH} t_{PHL}	Propagation Delay D_N to Y_N (LE = HIGH)	C_L = 50 pF R_L = 500Ω	1.5	9.0	ns
		C_L = 300 pF[3] R_L = 500Ω	1.5	8.0	ns
t_{SU}	Set-up Time Data to LE	C_L = 50 pF R_L = 500Ω	2.5	—	ns
t_H	Hold Time Data to LE		2.5	—	ns
t_{PLH} t_{PHL}	Propagation Delay LE to Y_N	C_L = 50 pF R_L = 500Ω	1.5	12.0	ns
		C_L = 300 pF[3] R_L = 500Ω	—	16.0	ns
t_W	LE Pulse Width (HIGH)	C_L = 50 pF R_L = 500Ω	4.0	—	ns
t_{PZH} t_{PZL}	Output Enable Time $\overline{OE}$ to Y_N	C_L = 50 pF R_L = 500Ω	1.5	10.0	ns
		C_L = 300 pF[3] R_L = 500Ω	1.5	23.0	ns
t_{PHZ} t_{PLZ}	Output Disable Time $\overline{OE}$ to Y_N	C_L = 50 pF R_L = 500Ω	1.5	7.0	ns
		C_L = 5 pF[3] R_L = 500Ω	1.5	8.0	ns

Notes:
1. See test circuit and wave forms.
2. Minimum limits are guaranteed but not tested on Propagation Delays.
3. This parameter is guaranteed but not production tested.

Capacitance (T_A = 25°C, f = 1 MHz)

Parameters[1]	Description	Test Conditions	Typ	Max.	Units
C_{IN}	Input Capacitance	V_{IN} = 0 V	4.5	6	pF
C_{OUT}	Output Capacitance	V_{OUT} = 0 V	5.5	8	pF

Note:
1. This parameter is determined by device characterization but is not production tested.